

# 2N5194, 2N5195

Preferred Devices

## Silicon PNP Power Transistors

These devices are designed for use in power amplifier and switching circuits; excellent safe area limits. Complement to NPN 2N5191, 2N5192.

### Features

- Pb-Free Packages are Available\*

### MAXIMUM RATINGS (Note 1)

Rating	Symbol	2N5194	2N5195	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	80	Vdc
Collector-Base Voltage	$V_{CB}$	60	80	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0		Vdc
Collector Current	$I_C$	4.0		Adc
Base Current	$I_B$	1.0		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	40	320	W W/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150		°C/W

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{JC}$	3.12	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC registered data.



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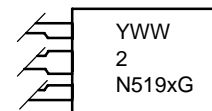
<http://onsemi.com>

**4 AMPERE  
POWER TRANSISTORS  
PNP SILICON  
60 – 80 VOLTS**



**TO-225AA  
CASE 77-09  
STYLE 1**

### MARKING DIAGRAM



Y = Year  
 WW = Work Week  
 2N519x = Device Code  
 x = 4 or 5  
 G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
2N5194	TO-225	500 Units / Bulk
2N5194G	TO-225 (Pb-Free)	500 Units / Bulk
2N5195	TO-225	500 Units / Bulk
2N5195G	TO-225 (Pb-Free)	500 Units / Bulk

Preferred devices are recommended choices for future use and best overall value.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N5194, 2N5195

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage (Note 3) ( $I_C = 0.1\text{ Adc}$ , $I_B = 0$ )	$V_{CEO(sus)}$	60 80	– –	Vdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 80\text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	– –	1.0 1.0	mAdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ ) ( $V_{CE} = 80\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ ) ( $V_{CE} = 60\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ , $T_C = 125^\circ\text{C}$ ) ( $V_{CE} = 80\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ , $T_C = 125^\circ\text{C}$ )	$I_{CEX}$	– – – –	0.1 0.1 2.0 2.0	mAdc
Collector Cutoff Current ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 80\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	– –	0.1 0.1	mAdc
Emitter Cutoff Current ( $V_{BE} = 5.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	1.0	mAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (Note 3) ( $I_C = 1.5\text{ Adc}$ , $V_{CE} = 2.0\text{ Vdc}$ )  ( $I_C = 4.0\text{ Adc}$ , $V_{CE} = 2.0\text{ Vdc}$ )	$h_{FE}$	25 20 10 7.0	100 80 – –	–
Collector–Emitter Saturation Voltage (Note 3) ( $I_C = 1.5\text{ Adc}$ , $I_B = 0.15\text{ Adc}$ ) ( $I_C = 4.0\text{ Adc}$ , $I_B = 1.0\text{ Adc}$ )	$V_{CE(sat)}$	– –	0.6 1.4	Vdc
Base–Emitter On Voltage (Note 3) ( $I_C = 1.5\text{ Adc}$ , $V_{CE} = 2.0\text{ Vdc}$ )	$V_{BE(on)}$	–	1.2	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current–Gain — Bandwidth Product ( $I_C = 1.0\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$f_T$	2.0	–	MHz

2. Indicates JEDEC registered data.
3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

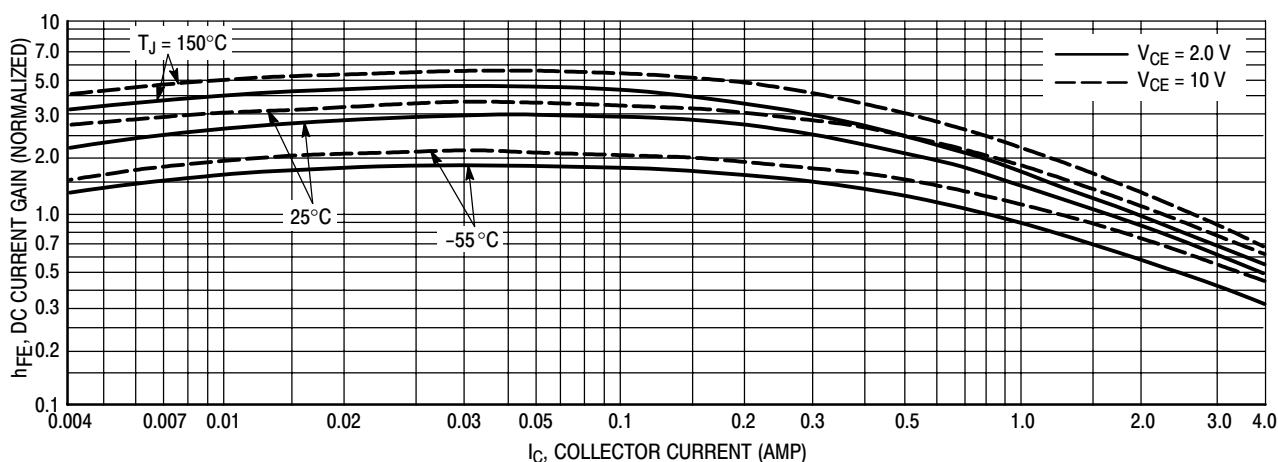
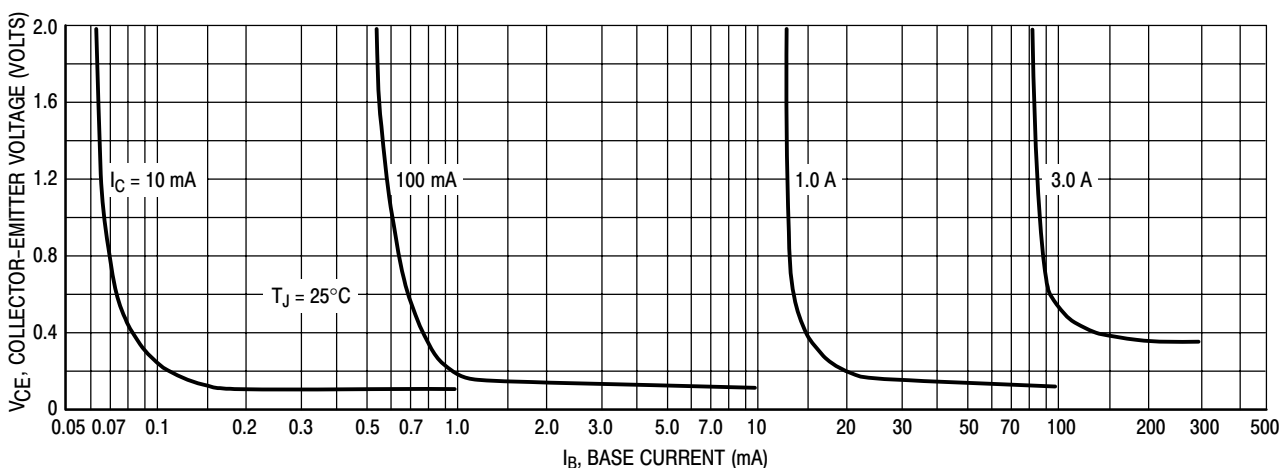
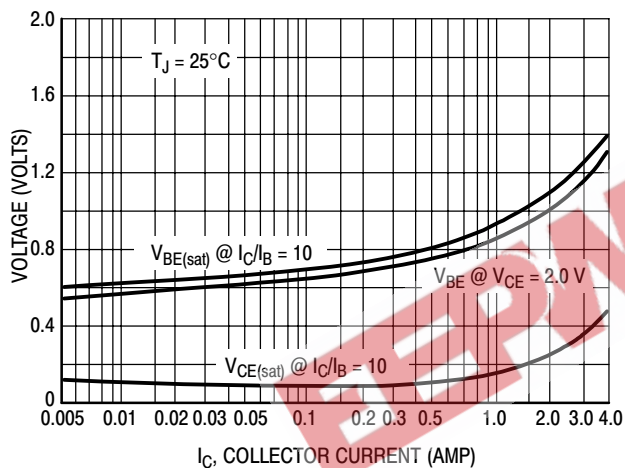


Figure 1. DC Current Gain

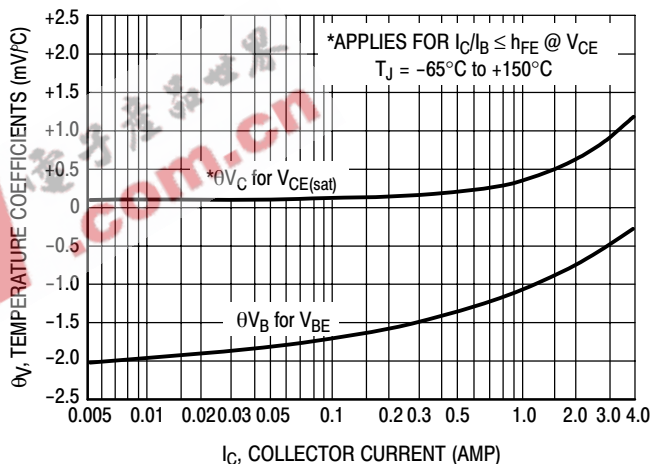
## 2N5194, 2N5195



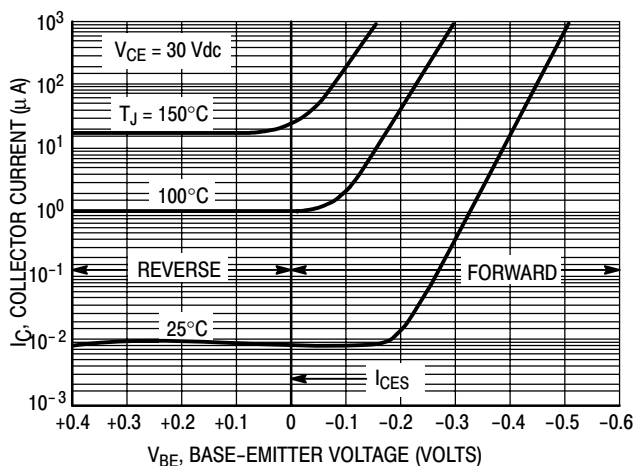
**Figure 2. Collector Saturation Region**



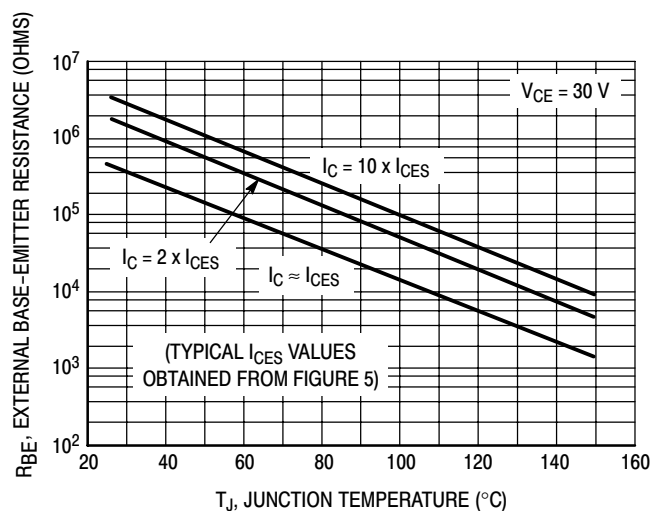
**Figure 3. "On" Voltage**



**Figure 4. Temperature Coefficients**



**Figure 5. Collector Cut-Off Region**



**Figure 6. Effects of Base-Emitter Resistance**

## 2N5194, 2N5195

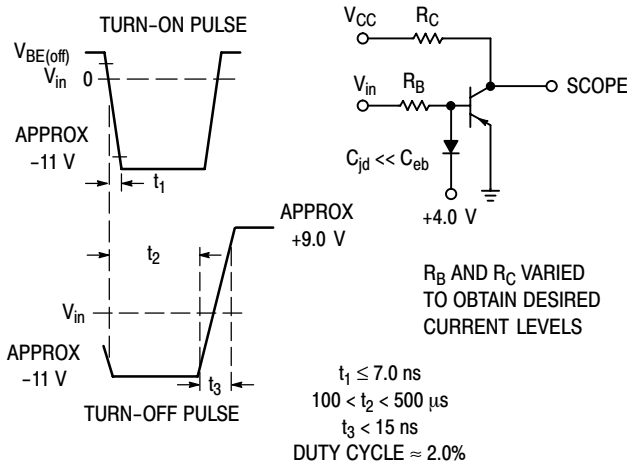


Figure 7. Switching Time Equivalent Test Circuit

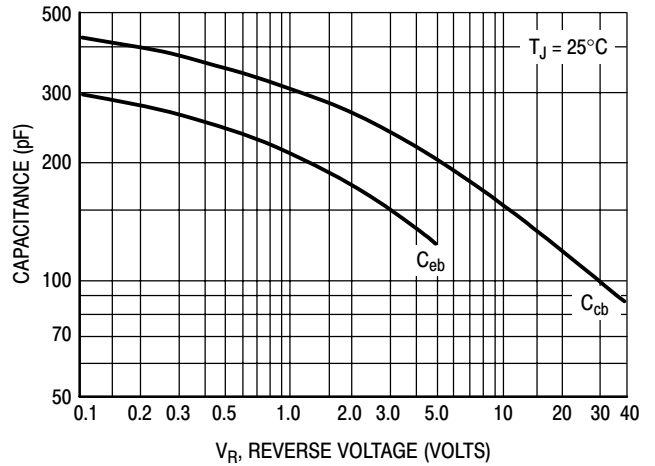


Figure 8. Capacitance

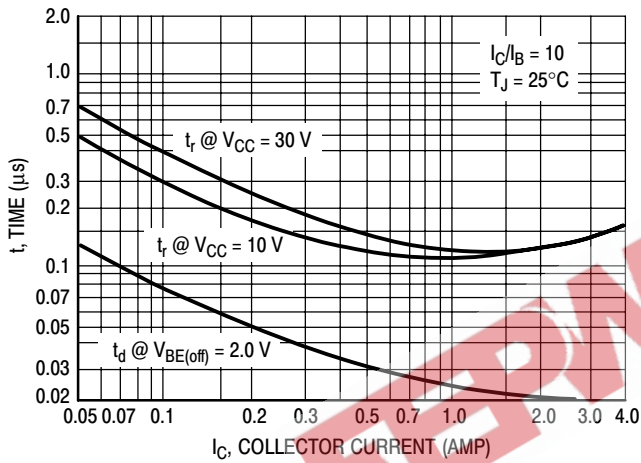


Figure 9. Turn-On Time

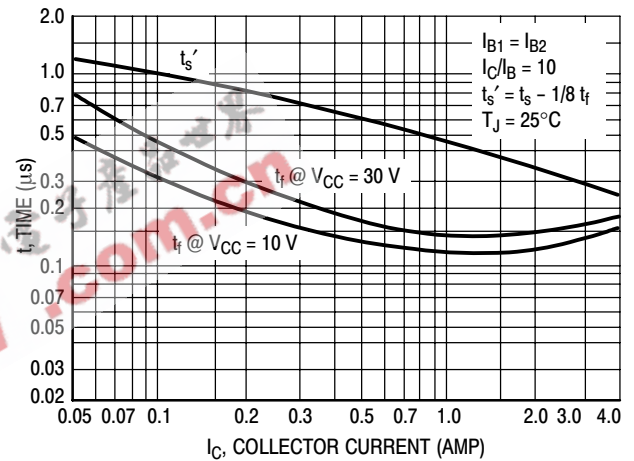


Figure 10. Turn-Off Time

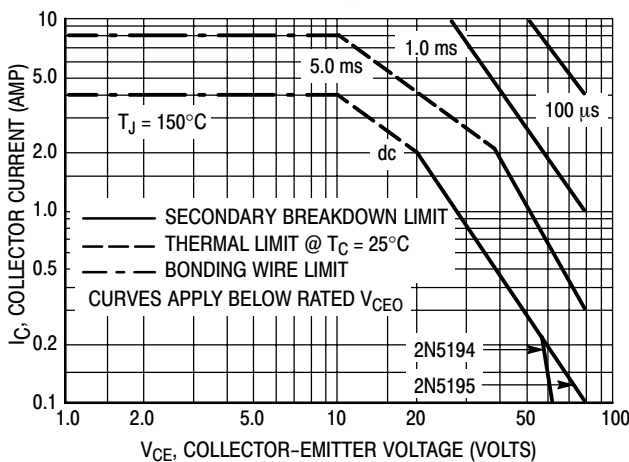


Figure 11. Rating and Thermal Data Active-Region Safe Operating Area

### Note 1:

There are two limitations on the power handling ability of a transistor; average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on  $T_{J(pk)} = 150^\circ\text{C}$ .  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ . At high-case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

## 2N5194, 2N5195

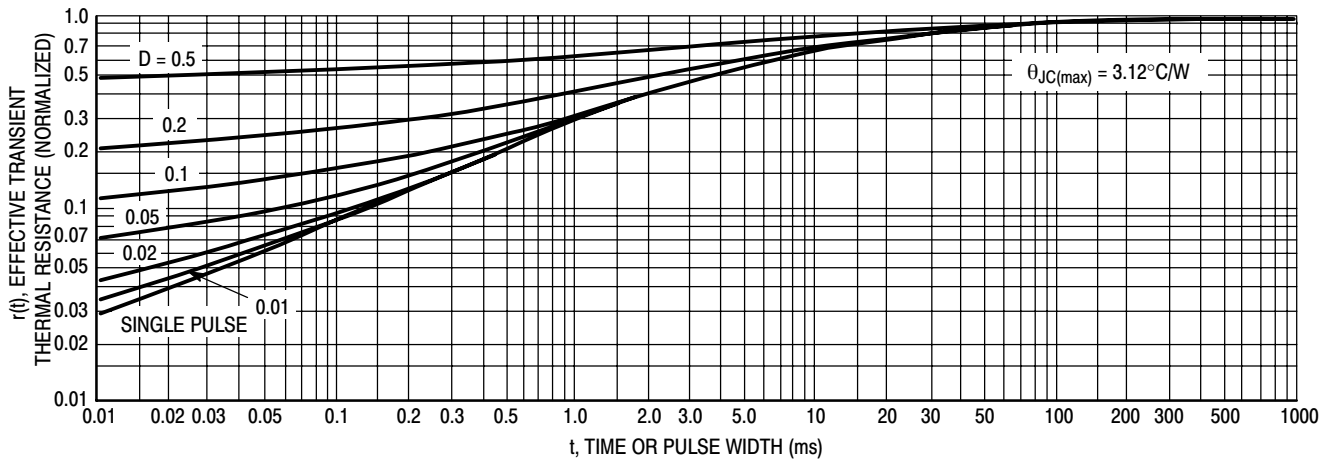


Figure 12. Thermal Response

### DESIGN NOTE: USE OF TRANSIENT THERMAL RESISTANCE DATA

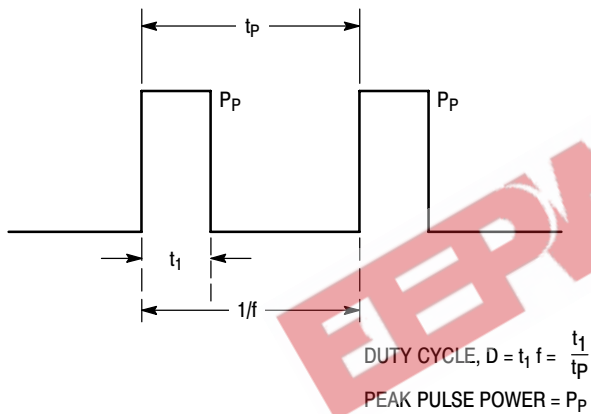


Figure 13.

A train of periodical power pulses can be represented by the model shown in Figure 13. Using the model and the device thermal response, the normalized effective transient thermal resistance of Figure 12 was calculated for various duty cycles.

To find  $\theta_{JC}(t)$ , multiply the value obtained from Figure 12 by the steady state value  $\theta_{JC}$ .

Example:

The 2N5193 is dissipating 50 watts under the following conditions:  $t_1 = 0.1$  ms,  $t_p = 0.5$  ms. ( $D = 0.2$ ).

Using Figure 12, at a pulse width of 0.1 ms and  $D = 0.2$ , the reading of  $r(t_1, D)$  is 0.27.

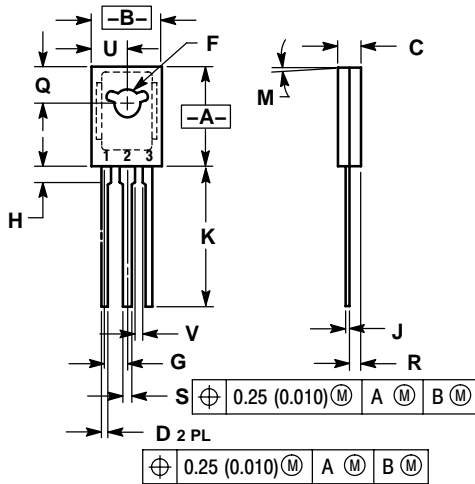
The peak rise in junction temperature is therefore:

$$\Delta T = r(t) \times P_p \times \theta_{JC} = 0.27 \times 50 \times 3.12 = 42.2^\circ\text{C}$$

# 2N5194, 2N5195

## PACKAGE DIMENSIONS

TO-225  
CASE 77-09  
ISSUE Z



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

**STYLE 1:**

1. EMITTER
2. COLLECTOR
3. BASE

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